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December 2013

FPAB30BH60

PFC SPM® 3 Series for Single-Phase Boost PFC

Features

- UL Certified No. E209204 (UL1557)
- 600 V 30 A Single-Phase Boost PFC with Integral Gate Driver and Protection
- Very Low Thermal Resistance Using Al₂O₃ DBC Substrate
- Full-Wave Bridge Rectifier and High-Performance Output Diode
- · Built-in NTC Thermistor for Temperature Monitoring
- · Optimized for 20kHz Switching Frequency
- · Isolation Rating: 2500 Vrms/min.

Applications

· Single-Phase Boost PFC Converter

Related Source

- · AN-9090 PFC SPM 3 Series User's Guide
- AN-9091 Boost PFC Inductor Design Guide

General Description

The FPAB30BH60 is a PFC SPM® 3 module providing a fully-featured, high-performance Boost PFC (Power Factor Correction) input power stage for consumer, medical, and industrial applications. These modules integrate optimized gate drive of the built-in IGBT to minimize EMI and losses. while also providing multiple on-module protection features including under-voltage lockout, over-current shutdown, thermal monitoring, and fault reporting. These modules also feature a full-wave rectifier, and high-performance output diode for additional space savings and mounting convenience

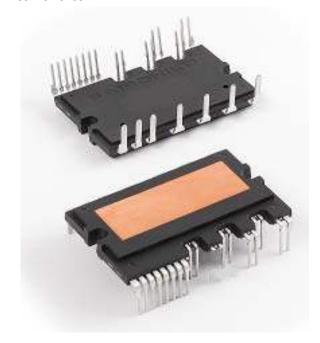


Figure 1. Package Overview

Package Marking & Ordering Information

Device	Device Marking	Package	Packing Type	Quantity
FPAB30BH60	FPAB30BH60	SPMIA-027	Rail	10

Integrated Power Functions

• PFC converter for single-phase AC / DC power conversion (please refer to Figure 3)

Integrated Drive, Protection, and System Control Functions

- For IGBTs: gate drive circuit, Over-Current Protection (OCP), control supply circuit Under-Voltage Lock-Out (UVLO) Protection
- · Fault signal: corresponding to OC and UV fault
- · Built-in thermistor: temperature monitoring
- Input interface: active-HIGH interface, works with 3.3 / 5 V logic, Schmitt-trigger input

Pin Configuration

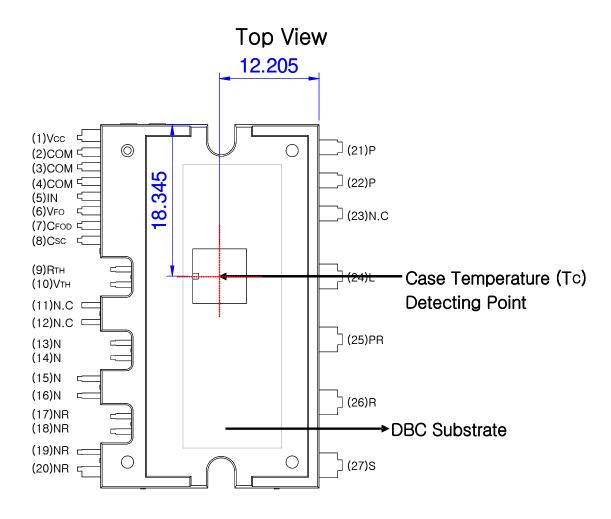


Figure 2. Top View

Notes :

1. For the measurement point of case temperature (T_C) , please refer to Figure 2.

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	V _{CC}	Common Bias Voltage for IC and IGBT Driving
2,3,4	COM	Common Supply Ground
5	IN	Signal Input for IGBT
6	V_{FO}	Fault Output
7	C _{FOD}	Capacitor for Fault Output Duration Selection
8	C _{SC}	Capacitor (Low-Pass Filter) for Over-Current Detection
9	R _(TH)	Series Resistor for The Use of Thermistor
10	V _(TH)	Thermistor Bias Voltage
11,12	N.C	No Connection*
13~16	N	IGBT Emitter
17~20	N _R	Negative DC-Link of Rectifier
21,22	Р	Positive Rail of DC-Link
23	N.C	No Connection
24	L	Reactor Connection Pin
25	P _R	Positive DC-Link of Rectifier
26	R	AC Input for R-Phase
27	S	AC Input for S-Phase

^{* 11}th and 12th pins are cut. Please refer to package outline drawings for more detail.

Internal Equivalent Circuit and Input/Output Pins

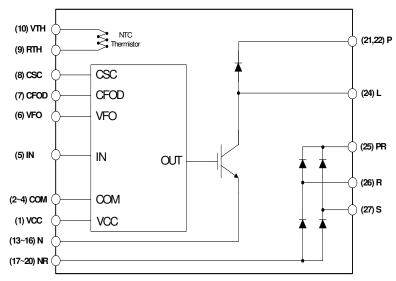


Figure 3. Internal Block Diagram

Absolute Maximum Ratings ($T_J = 25$ °C, unless otherwise specified.)

Converter Part

Symbol	Item	Condition	Rating	Unit
V _i	Supply Voltage	Applied between R - S	264	V _{rms}
V _{i(Surge)}	Supply Voltage (Surge)	Applied between R - S	500	٧
V _{PN}	Output Voltage	Applied between P - N	450	٧
V _{PN(Surge)}	Output Voltage (Surge)	Applied between P - N	500	V
V _{CES}	Collector - Emitter Voltage		600	٧
I _{FSM}	Peak Forward Surge Current	Single Half Sine-Wave	250	Α
l _i	Input Current (100% Load)	$T_C < 95^{\circ}C$, $V_i = 220 \text{ V}$, $V_{PN} = 390 \text{ V}$, $V_{PWM} = 20 \text{ kHz}$	25	Α
I _{i(125%)}	Input Current (125% Load)	T_C < 95°C, V_i = 220 V, V_{PN} = 390 V, V_{PWM} = 20 kHz, 1 Minite Non-Repetitive	30	Α
P _C	Collector Dissipation	T _C = 25°C	169	W
T _J	Operating Junction Temperature		-20 ~ 150	°C

Control Part

Symbol	Item	Condition	Rating	Unit
V _{CC}	Control Supply Voltage	Applied between V _{CC} - COM	20	V
V _{IN}	Input Signal Voltage	Applied between IN - COM	-0.3 ~ V _{CC} +0.3	V
V _{FO}	Fault Output Supply Voltage	Applied between V _{FO} - COM	-0.3 ~ V _{CC} +0.3	٧
I _{FO}	Fault Output Current	Sink Current at V _{FO} Pin	5	mA
V _{SC}	Current Sensing Input Voltage	Applied between C _{SC} - COM	-0.3 ~ V _{CC} +0.3	V

Total System

Symbol	Item	Condition	Rating	Unit
T _C	Module Case Operating Temperature		-20 ~ 100	°C
T _{STG}	Storage Temperature		-40 ~ 125	°C
V _{ISO}	Isolation Voltage	60 Hz, Sinusoidal, AC 1 Minute, Connect Pins to Heat Sink Plate	2500	V _{rms}

Thermal Resistance

Symbol	Item	Condition	Min.	Тур.	Max.	Unit
$R_{\theta(j-c)Q}$	Junction to Case Thermal Resistance	IGBT	-	-	0.74	°C/W
$R_{\theta(j-c)F}$		FRD	-	-	1.44	°C/W
$R_{\theta(j-c)R}$		Rectifier (per 1 / 4 module)	-	-	2.07	°C/W

Notes:

2. For the measurement point of case temperature($T_{\mbox{\scriptsize C}}$), please refer to Figure 2.

^{1.} The maximum junction temperature rating of the power chips integrated within the PFC SPM product is 150 °C(@T_C \leq 100°C). However, to insure safe operation of the PFC SPM product, the average junction temperature should be limited to $T_{J(ave)} \leq 125$ °C (@T_C \leq 100°C)

Electrical Characteristics (T_J = 25°C, Unless Otherwise Specified.)

Converter Part

Symbol	Item	Condition	Min.	Тур.	Max.	Unit
V _{CE(SAT)}	IGBT Saturation Voltage	$V_{CC} = 15 \text{ V}, V_{IN} = 5 \text{ V}, I_{C} = 30 \text{ A}$	-	2.0	2.8	V
V _{FF}	FRD Forward Voltage	I _F = 30 A	-	1.8	2.5	٧
V _{FR}	Rectifier Forward Voltage	I _F = 30 A	-	1.2	1.5	V
t _{ON}	Switching Times	$V_{PN} = 400 \text{ V}, V_{CC} = 15 \text{V}, I_{C} = 30 \text{ A}$	-	650	-	ns
t _{C(ON)}		$V_{IN} = 0 \text{ V} \leftrightarrow 5 \text{ V}$, Inductive Load	-	400	-	ns
t _{OFF}		(Note 3)	-	620	-	ns
t _{C(OFF)}			-	200	-	ns
t _{rr}			-	60	-	ns
I _{rr}			-	3.5	-	Α
I _{CES}	Collector - Emitter Leakage Current	V _{CE} = V _{CES}	-	-	250	μА

^{3.} t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. t_{C(ON)} and t_{C(OFF)} are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

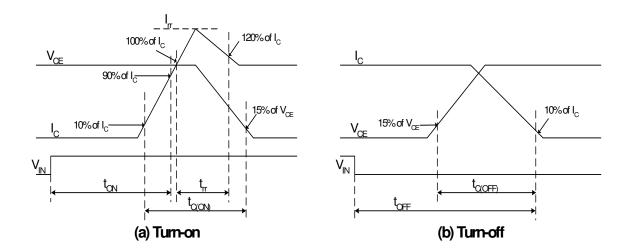


Figure 4. Switching Time Definition

Control Part

Symbol	Item	Con	ndition	Min.	Тур.	Max.	Unit
I _{QCCL}	Quiescent V _{CC} Supply Current	V _{CC} = 15 V, IN = 0 V	V _{CC} - COM	-	-	26	mA
V_{FOH}	Fault Output Voltage	V _{SC} = 0 V, V _{FO} Circuit:	4.7 kΩ to 5 V Pull-up	4.5	-	-	٧
V _{FOL}		V _{SC} = 1 V, V _{FO} Circuit:	4.7 k Ω to 5 V Pull-up	-	-	0.8	٧
V _{SC(ref)}	Over-Current Trip Level	V _{CC} = 15 V		0.45	0.5	0.55	٧
UV _{CCD}	Supply Circuit Under-Voltage	Detection Level		10.7	11.9	13.0	٧
UV _{CCR}	Protection	Reset Level		11.2	12.4	13.2	٧
t _{FOD}	Fault-Out Pulse Width	C _{FOD} = 33 nF (Note 3)		1.4	1.8	2.0	ms
V _{IN(ON)}	ON Threshold Voltage	Applied between IN - COM		2.8	-	ı	٧
V _{IN(OFF)}	OFF Threshold Voltage			-	-	0.8	٧
R _{TH}	Resistance of Thermistor	at T _{TH} = 25°C (Note 4, Figure 5)		-	50	ı	kΩ
		at T _{TH} = 100°C (Note 4	I, Figure 5)	-	2.99	-	kΩ

Notes:

3. The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation: $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[F]$

 $4.\ T_{TH}\ is\ the\ temperature\ of\ know\ case\ temperature\ (T_C),\ please\ make\ the\ experiment\ considering\ your\ application.$



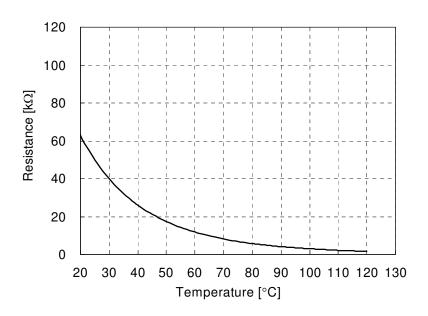


Figure 5. R-T Curve of the Built-In Thermistor

Recommended Operating Condition

Symbol	Item	Condition	Min.	Тур.	Max.	Unit
V _i	Input Supply Voltage	Applied between R - S	187	220	253	V_{rms}
V _{PN}	Output Voltage	Applied between P - N	-	380	400	٧
V _{CC}	Control Supply Voltage	Applied between V _{CC(L)} - COM	13.5	15.0	16.5	٧
dV _{CC} /dt	Control Supply Variation		-1	-	1	V/μs
f _{PWM}	PWM Input Frequency	T _J ≤ 150°C	-	20	-	kHz
l _i	Allowable Input Current	T _C < 90°C, V _i = 220 V, V _{PN} = 380 V V _{PWM} = 20 kHz	-	-	30	A _{peak}

Mechanical Characteristics and Ratings

Item	Co	Condition			Max.	Unit
Mounting Torque	Mounting Screw: M3	Recommended 0.62 N•m	0.51	0.62	0.72	N•m
Device Flatness	See Figure 6		0	-	+120	μm
Weight			-	15.00	-	g

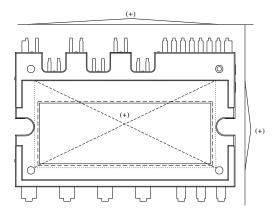
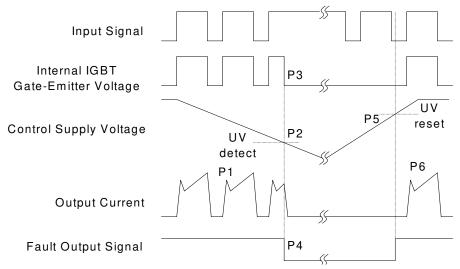


Figure 6. Flatness Measurement Position

Time Charts of Protective Function

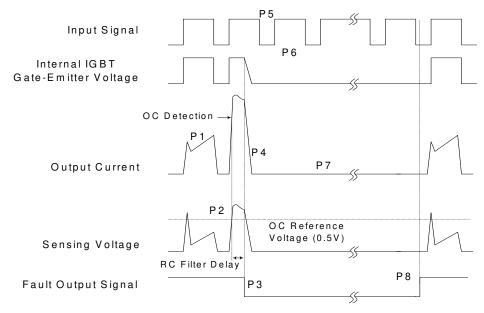


P1: Normal operation: IGBT ON and conducting current

P2 : Under-voltage detection P3 : IGBT gate interrupt P4 : Fault signal generation P5 : Under-voltage reset

P6: Normal operation: IGBT ON and conducting current

Figure 7. Under-Voltage Protection



P1: Normal operation: IGBT ON and conducting current

P2 : Over current detection

P3: IGBT gate interrupt / fault signal generation

P4: IGBT is slowly turned off

P5: IGBT OFF signal

P6: IGBT ON signa: but IGBT cannot be turned on during the fault output activation

P7: IGBT OFF state

P8 : Fault output reset and normal operation start

Figure 8. Over-Current Protection

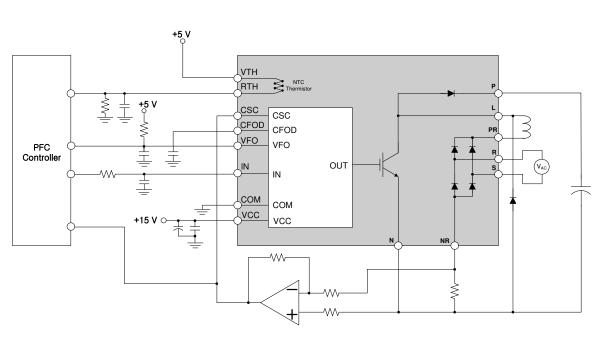
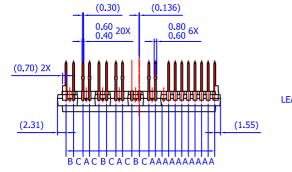


Figure 9. Application Example

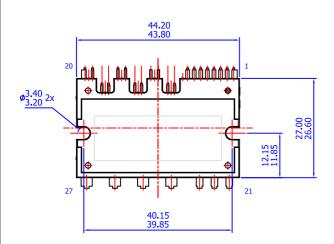
Notes:

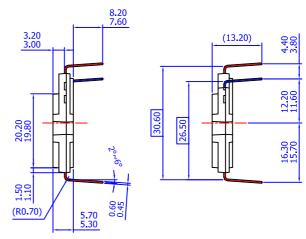
- 5. Each capacitors should be located as close to PFC SPM® product pins as possible. 6. It's recommended that anti-parallel diode should be connected with IGBT.

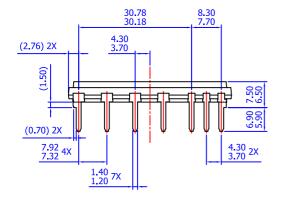


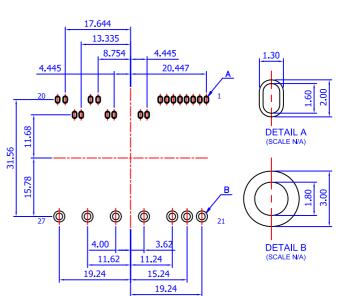
LEAD PITCH (TOLERANCE: ±0.30)

A: 1.778 B: 2.050 C: 2.531









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